



Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No. SDK1P007	Application No.: 10/039,615
	Applicant: WALLACE	
	Filing Date 01/04/2002	Group 2811

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
qv	A	5,408,127	4/18/95	Mostafazadeh			
qv	B	4,818,895	4/4/89	Kaufman			
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	H						
	I						

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Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
qv	J	WO02/08257	10/17/02	WIPO				
qv	K	EP0753891	1/15/97	EPO				
	L							
	M							
	N							

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
qv	O	Nakanishi et al., "Development of High Density Memory IC Package by Stacking IC Chips," Abstract No. XP000624986, IEEE, Vol. Conf. 45, Pages 634-640 (1995)
qv	P	Patent Abstract of Japan, Pub No. 63219131, Pub Date 9/12/88, 2 Pages
	Q	
Examiner <i>Amun</i>		Date Considered 01/12/04

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.